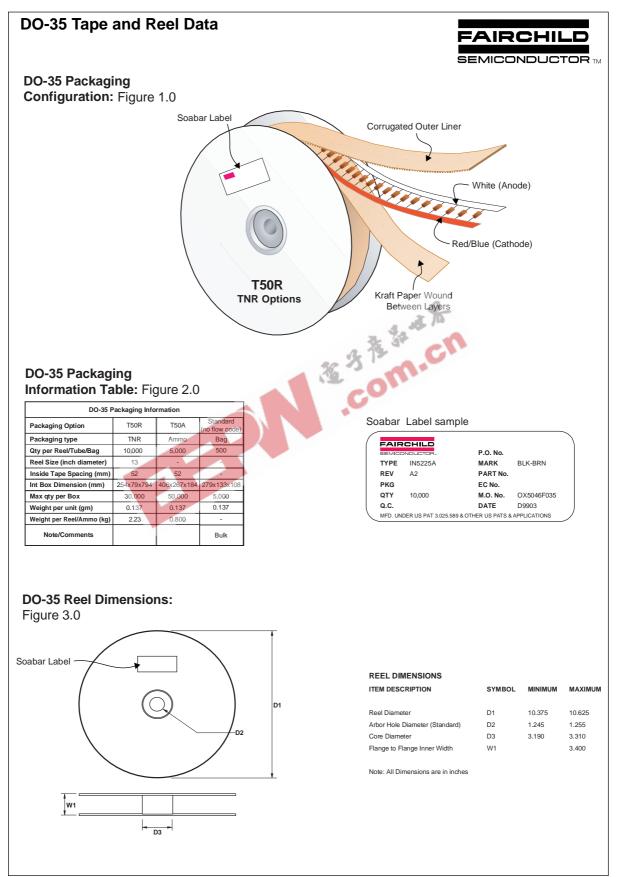
	NDUCTOR TM		
	FDH/FDLL 30	00/A / 333	
l	DO-35	FDLL300 BROWN FDLL300A BROWN FDLL333 BROWN	RKING 2ND BAND GREEN YELLOW BLUE
Hiah	Conductance Low Leakage	Diada	
Sourced fr	rom Process 1M. See MMBD1501/A-1505/A for cha ute Maximum Ratings* TA = 25°C un	aracteristics.	
Sourced fr Absolu ymbol	rom Process 1M. See MMBD1501/A-1505/A for cha ute Maximum Ratings* TA = 25°C un Parameter	eracteristics.  less otherwise noted Value	Units
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Sourced fr Absolu ymbol	rom Process 1M. See MMBD1501/A-1505/A for cha ute Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current	aracteristics. less otherwise noted Value 125 200	V mA
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Sourced fi Absolu ymbol	rom Process 1M. See MMBD1501/A-1505/A for cha ute Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current	aracteristics. less otherwise noted Value 125 200	V mA
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Sourced fr Absolu Symbol (IV surge)	rom Process 1M. See MMBD1501/A-1505/A for cha <b>Ute Maximum Ratings*</b> TA = 25°C un <b>Parameter</b> Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond Storage Temperature Range Operating Junction Temperature	Value           125           200           500           600           1.0           4.0           -65 to +200           175	V mA mA MA A A
Sourced fr Absolu Symbol V <sub>IV</sub> (surge) stg J *These rating NOTES: 1) These ratin 2) These are	rom Process 1M. See MMBD1501/A-1505/A for cha <b>Ute Maximum Ratings*</b> TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond Storage Temperature Range	eracteristics.	V mA mA MA A A A C
Sourced fr Absolu Symbol VIV Surge) stg J *These rating NOTES: 1) These rating 2) These rating These rating	rom Process 1M. See MMBD1501/A-1505/A for cha <b>Ite Maximum Ratings*</b> TA = 25°C un <b>Parameter</b> Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond Storage Temperature Range Operating Junction Temperature gs are lainting values above which the serviceability of any semicond steady state limits. The factory should be consulted on applications in	eracteristics.	V mA mA MA A A C °C °C
Sourced fr Absolu Symbol V <sub>IV</sub> (surge) *These rating NOTES: 1) These ratin 2) These ratin	rom Process 1M. See MMBD1501/A-1505/A for cha <b>Ite Maximum Ratings*</b> TA = 25°C un <b>Parameter</b> Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond Storage Temperature Range Operating Junction Temperature gs are limiting values above which the serviceability of any semicond ings are based on a maximum junction temperature of 200 degrees C steady state limits. The factory should be consulted on applications in <b>al Characteristics</b> TA = 25°C unless other	Aracteristics.  Less otherwise noted	V mA mA MA A A A C
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Sourced fr Absolu Symbol V <sub>IV</sub> 0 (surge) stg J *These rating NOTES: 1) These ratin 2) These are	rom Process 1M. See MMBD1501/A-1505/A for cha <b>Ite Maximum Ratings*</b> TA = 25°C un <b>Parameter</b> Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond Storage Temperature Range Operating Junction Temperature gs are limiting values above which the serviceability of any semicond ings are based on a maximum junction temperature of 200 degrees C steady state limits. The factory should be consulted on applications in <b>al Characteristics</b> TA = 25°C unless other	Aracteristics.  Less otherwise noted	V mA mA MA A A °C °C °C

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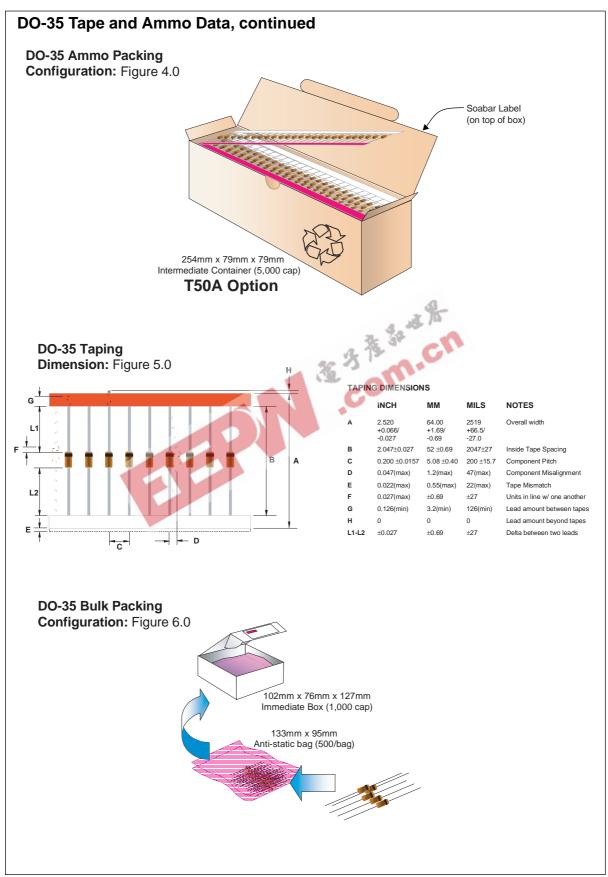
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Symbol	Para	meter	Test Conditions	Min	Max	Units
Bv	Breakdown Voltage	e	I <sub>R</sub> = 100 μA	150		V
I <sub>R</sub>	Reverse Current	FDH/FDLL 300/A	V <sub>R</sub> = 125 V		1.0	nA
			$V_{R} = 125 V, T_{A} = 150^{\circ}C$		3.0	μA
		FDH/FDLL 333	$V_{R} = 125 V$		3.0	nA
	Famural Valtana		$V_{\rm R} = 125 \text{ V},  \text{T}_{\rm A} = 100^{\circ}\text{C}$		500	nA
V <sub>F</sub>	Forward Voltage	FDH/FDLL 300/A FDH/FDLL 300	I <sub>F</sub> = 1.0 mA I <sub>F</sub> = 5.0 mA		680 750	mV mV
		FDH/FDLL 300A	$I_F = 5.0 \text{ mA}$ $I_F = 5.0 \text{ mA}$		760	mV
		FDH/FDLL 300/A	$I_{\rm F} = 10  {\rm mA}$		800	mV
		FDH/FDLL 300	$I_F = 50 \text{ mA}$		880	mV
		FDH/FDLL 300A	$I_{\rm F} = 50  \rm mA$		890	mV
		FDH/FDLL 300/A	$I_{\rm F} = 100  {\rm mA}$		920	mV
		FDH/FDLL 300/A	I <sub>F</sub> = 200 mA		1.0	V
		FDH/FDLL 333	I <sub>F</sub> = 50 mA	800	890	mV
			I <sub>F</sub> = 100 mA	830	940	mV
			I <sub>F</sub> = 150 mA	860	970	mV
			I <sub>F</sub> = 200 mA	0.87	1.05	V
			I <sub>F</sub> = 250 mA	0.88	1.08	V
0	Diada Caracitara		$I_F = 300 \text{ mA}$	0.9	1.15	V v
Co	Diode Capacitance	9	V <sub>R</sub> = 0, f = 1.0 MHz		6.0	pF

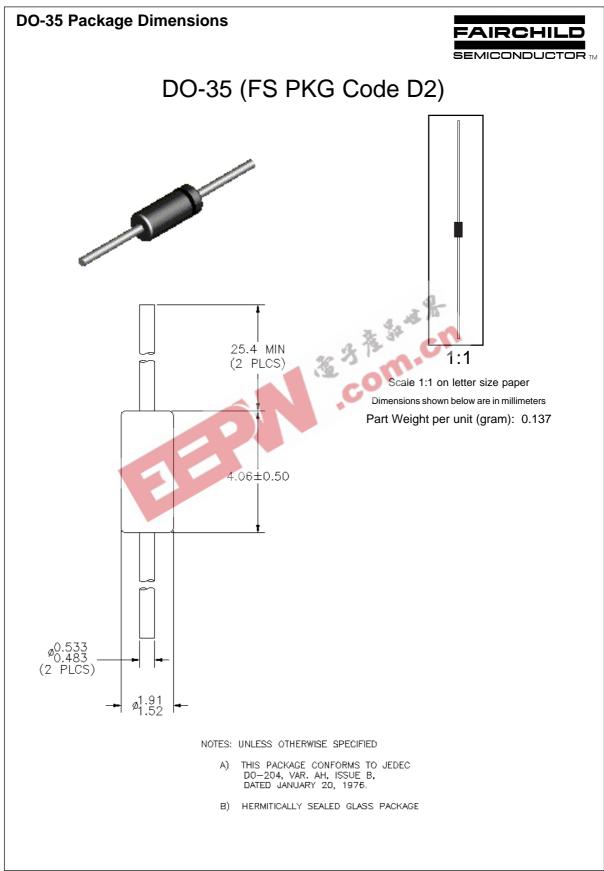
FDH300/A / FDLL300/A / FDH333 / FDLL333

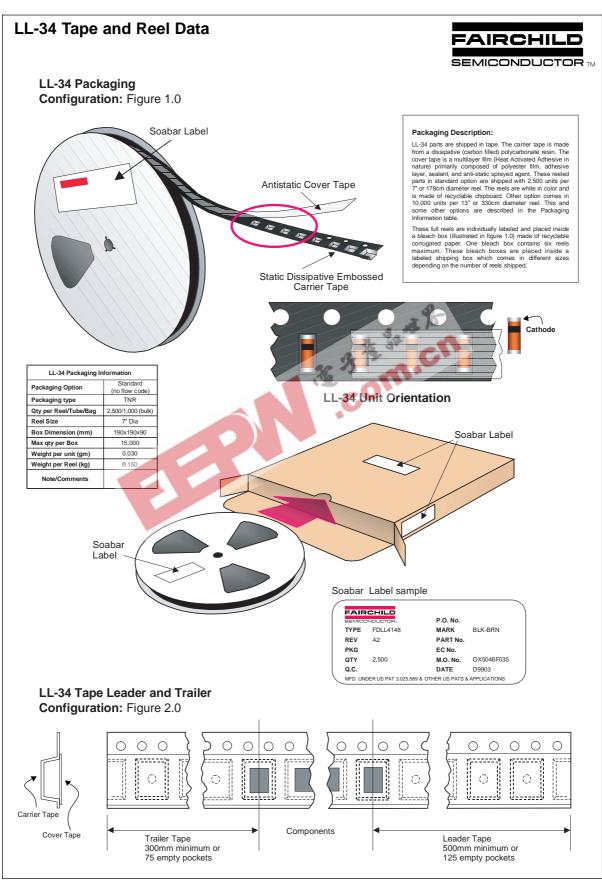


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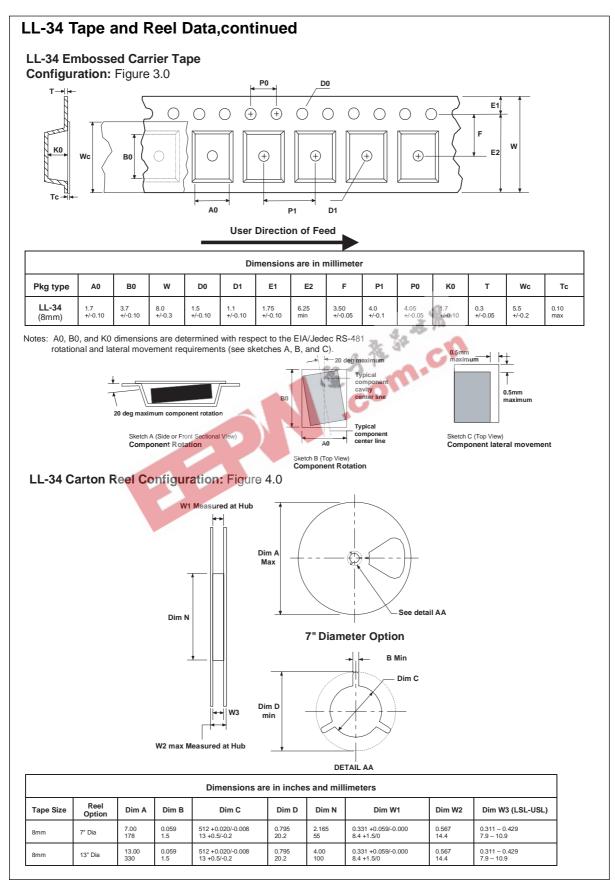
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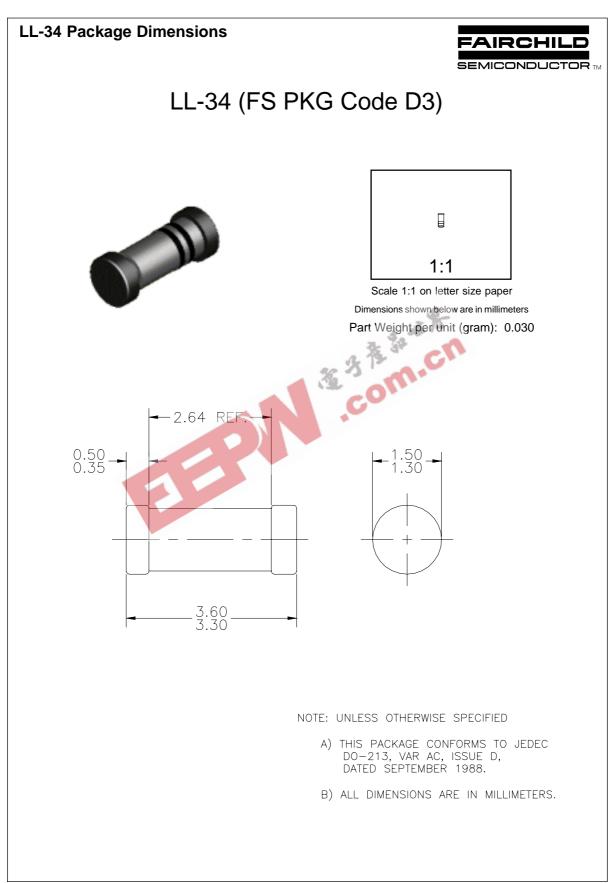


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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

# **PRODUCT STATUS DEFINITIONS**

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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